



#### **60V N-CHANNEL ENHANCEMENT MODE MOSFET**

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>A</sub> = +25°C	
60V	16mΩ @ V <sub>GS</sub> = 10V	9.2A	
60 V	$21m\Omega @ V_{GS} = 4.5V$	7.5A	

### **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>), maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load Switch
- Adaptor Switch
- Notebook PC

#### **Features and Benefits**

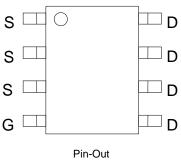
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

#### **Mechanical Data**

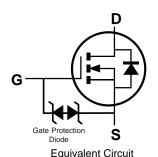
- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.076 grams (Approximate)







Top View



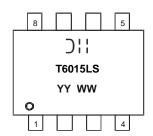
### **Ordering Information** (Note 4)

Part Number	Case	Packaging	
DMT6015LSS-13	SO-8	2,500/Tape & Reel	

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



) | | = Manufacturer's Marking T6015LS = Product Type Marking Code YYWW = Date Code Marking YY or  $\overline{YY}$  = Year (ex: 16 = 2016) WW = Week (01 - 53)



## **Maximum Ratings** (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Units		
Drain-Source Voltage	V <sub>DSS</sub>	60	V		
Gate-Source Voltage			V <sub>GSS</sub>	±16	V
Continuous Dunin Comment (Note C) // 401/	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	9.2 7.4	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	t<10s	T <sub>A</sub> = +25°C T <sub>A</sub> = +70°C	I <sub>D</sub>	11.9 9.5	Α
Continuous Drain Current (Note C) // 45/	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	7.5 6.0	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V	t<10s	$T_A = +25$ °C $T_A = +70$ °C	I <sub>D</sub>	9.7 7.7	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%	I <sub>DM</sub>	60	Α		
Maximum Continuous Body Diode Forward Curren	Is	2	А		
Avalanche Current, L = 0.1mH			I <sub>AS</sub>	15	А
Avalanche Energy, L = 0.1mH			Eas	11	mJ

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		$P_{D}$	1.5	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	D	85	°C/W
Thermal Resistance, Junction to Ambient (Note 5)	t<10s	$R_{\theta JA}$	45	°C/W
Total Power Dissipation (Note 6)		$P_D$	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	ם	74	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	$R_{\theta JA}$	37	°C/W
Thermal Resistance, Junction to Case		$R_{ heta JC}$	13	°C/W
Operating and Storage Temperature Range		$T_{J_1}T_{STG}$	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

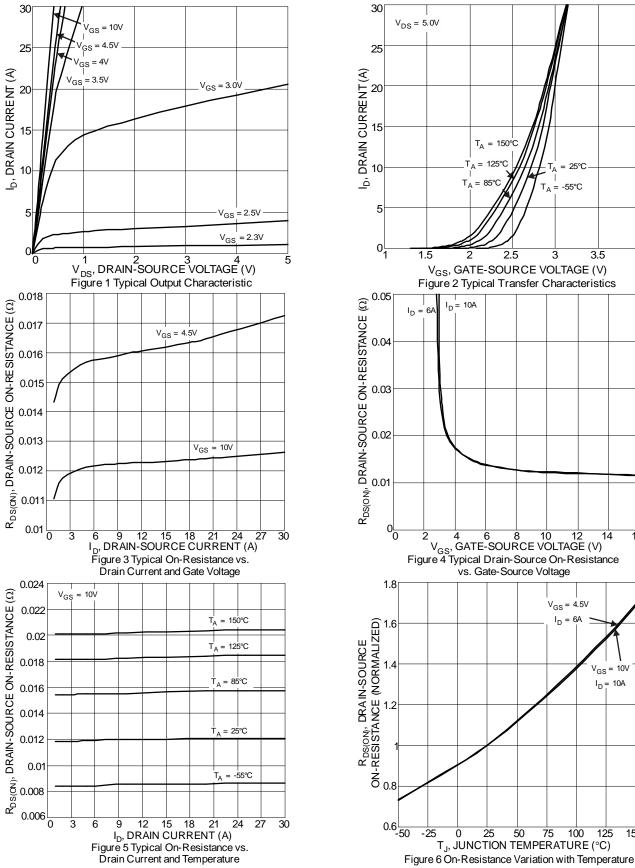
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	1	μΑ	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	0.5	_	2.5	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	
Static Drain-Source On-Resistance		_	12.4	16	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A	
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	15.8	21	11122	VGS = 4.5V, ID = 6A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.7	1.2	V	$V_{GS} = 0V, I_{S} = 1A$	
DYNAMIC CHARACTERISTICS (Note 8)				_			
Input Capacitance	C <sub>ISS</sub>	_	1,103	_		$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Output Capacitance	Coss	_	251	_	pF		
Reverse Transfer Capacitance	C <sub>RSS</sub>	_	20	_			
Gate Resistance	R <sub>G</sub>	_	1.5	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	$Q_{G}$	_	8.9	_		V 99V I 49A	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_G$	_	18.9	_	~0		
Gate-Source Charge	Q <sub>GS</sub>	_	3.0	_	nC	$V_{DS} = 30V, I_{D} = 10A$	
Gate-Drain Charge	$Q_{GD}$	_	2.8	_			
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.1	_		$V_{GS} = 10V, V_{DS} = 30V,$ $R_G = 6\Omega, I_D = 10A$	
Turn-On Rise Time	t <sub>R</sub>	_	7.1	_			
Turn-Off Delay Time	t <sub>D(OFF)</sub>	_	19.5	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	8.6	_			
Reverse Recovery Time	T <sub>RR</sub>	_	21.2	_	ns	1 101 11/11 1001/	
Reverse Recovery Charge	Q <sub>RR</sub>	_	13.2	_	nC	$I_F = 10A$ , di/dt = 100A/ $\mu$ s	

5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

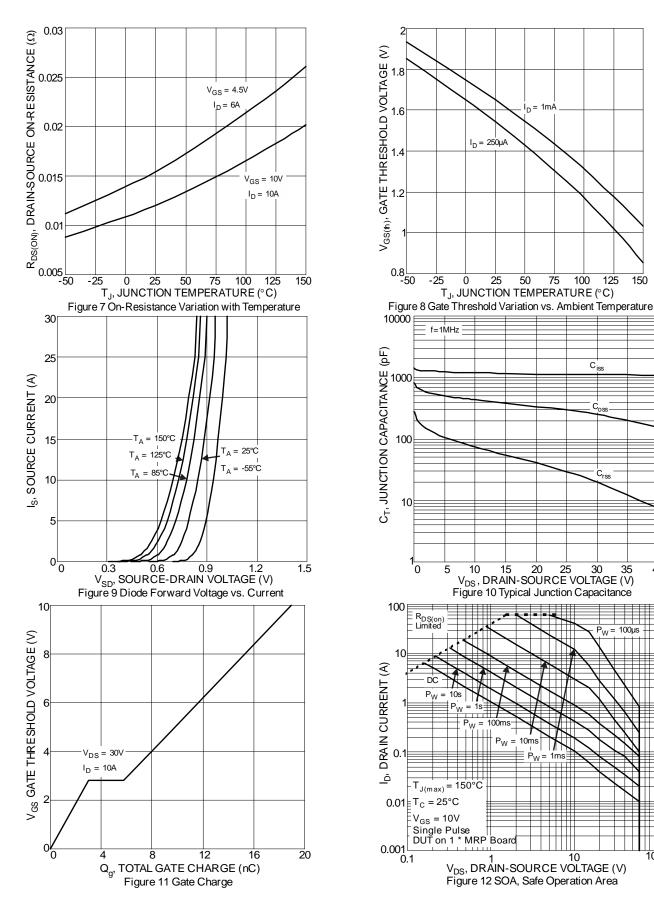
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.





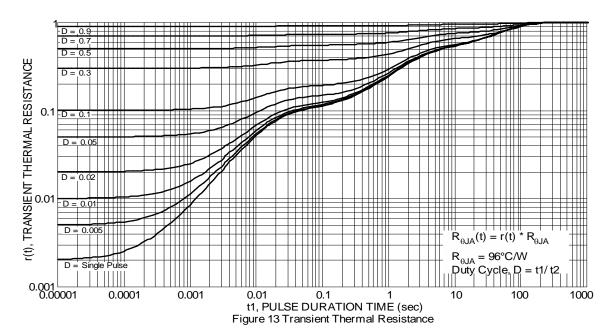




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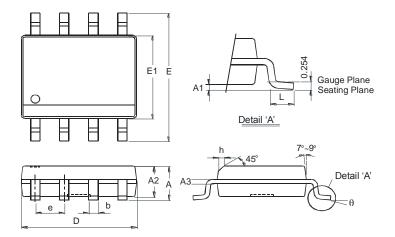




## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

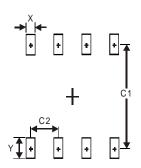
**SO-8** 



	SO-8				
Dim	Min	Max			
Α	_	1.75			
<b>A</b> 1	0.10	0.20			
A2	1.30	1.50			
A3	0.15	0.25			
b	0.3	0.5			
D	4.85	4.95			
Е	5.90	6.10			
E1	3.85	3.95			
е	1.27 Typ				
h	_	0.35			
L	0.62	0.82			
θ	0°	8°			
All Dimensions in mm					

# Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



3	U	-	Ö

Dimensions	Value (in mm)
Х	0.60
Υ	1.55
C1	5.4
Ć	1 27



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